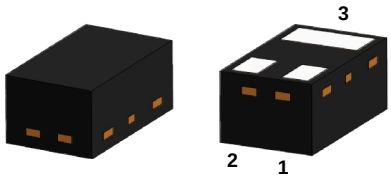
SOT-883 General Purpose Transistor
NPN Silicon
Surface Mount Plastic Package

Absolute Maximum Ratings (T_A = 25°C unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	40	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current	200	mA
P_D	Power Dissipation (FR-4 Board – minimum pad 25°C)	200	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	500	°C /W
T_J T_{STG}	Junction & Storage Temperature Range	-55 to +150	°C

These ratings are limiting values above which the serviceability of the device may be impaired.

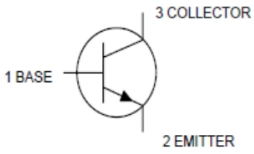


SOT-883 (DFN1006-3)

Specification Features:

- § DFN1006-3
- § Simplifies Circuit Design
- § RoHS Compliant
- § Green EMC
- § Matte Tin(Sn) Lead Finish
- § Weight: approx. 0.001g

Electrical Symbol:



Device Marking Code:

Device Type	Marking	Shipping
MMBT3904N3	C 1N E B	10,000/Reel

Electrical Characteristics (T_A = 25°C unless otherwise noted)

Off Characteristics

Symbol	Parameter	Test Condition	Limits		Unit
			Min	Max	
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage (Note 1)	I_C =1mA, I_B =0A	40	-	Volts
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C =10uA, I_E =0A	60	-	Volts
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E =10uA, I_B =0A	6	-	Volts
I_{CBO}	Collector Cutoff Current	V_{CB} =60V, I_E =0A	-	0.1	uA
I_{CEX}	Collector Cutoff Current	V_{CE} =30V, V_{EB} =3V	-	50	nA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V , I_C=0A		0.1	uA

Note 1: Pulse Test. Pulse width <300us, Duty cycle < 2.0%)

On Characteristics (Note 1)

Symbol	Parameter	Test Condition	Limits		Unit
			Min	Max	
H_{FE}	DC Current Dain	I_C =0.1mA, V_{CE} =1V	40	-	-
		I_C =1.0mA, V_{CE} =1V	70	-	
		I_C =10mA, V_{CE} =1V	100	300	
		I_C =50mA, V_{CE} =1V	60	-	
		I_C =100mA, V_{CE} =1V	30	-	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C=10mA, I_B=1mA	-	0.2	Volts
		I_C=50mA, I_B=5mA	-	0.3	
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C=10mA, I_B=1mA	0.65	0.85	Volts
		I_C=50mA, I_B=5mA	-	0.95	

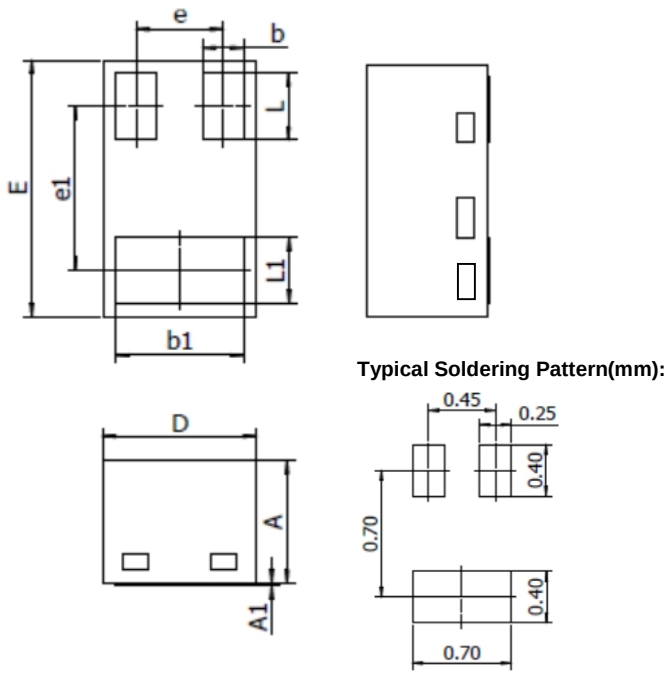
Small-signal Characteristics

Symbol	Parameter	Test Condition	Limits		Unit
			Min	Max	
f_T	Current-Gain-Bandwidth Product	I_C =10mA, V_{CE} =20V, f = 100MHz	200	-	MHz
C_{obo}	Output Capacitance	V_{CB} =5V, I_E =0A, f = 1.0MHz	-	4	pF
C_{ibo}	Input Capacitance	V_{BE} =0.5V, I_C =0A, f = 1.0MHz	-	8	pF
h_{ie}	Input Impedancen	V_{CE} =10V, I_C =1mA, f = 1.0kHz	1	10	kΩ
h_{re}	Voltage Feedback Ratio	V_{CE} =10V, I_C =1mA, f = 1.0kHz	0.5	8	$X10^{-4}$
h_{fe}	Small-signal Current Gain	V_{CE} =10V, I_C =1mA, f = 1.0kHz	100	400	-
h_{oe}	Output Admittance	V_{CE} =10V, I_C =1mA, f = 1.0kHz	1	40	θ mhos
NF	Noise Figure	V_{CE} =5V, I_C =100uA Rs=1.0kΩ f = 1.0kHz		5	dB

Switching Characteristics

Symbol	Parameter	Test Condition	Limits		Unit
			Min	Max	
t_d	Delay Time	V_{CC} =3V, V_{BE} =0.5V,	-	35	nS
t_r	Rise Time	I_C =10mA, I_{B1} =1mA	-	35	
t_s	Storage Time	V_{CC} =3V, I_C =10mA,	-	200	nS
t_f	Fall Time	I_{B1} = I_{B2} =1mA	-	50	

SOT-883 Package Outline



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.46	0.50	0.018	0.020
A1	---	0.03	---	0.001
D	0.55	0.65	0.022	0.026
E	0.95	1.05	0.037	0.041
b	0.12	0.22	0.005	0.008
b1	0.45	0.55	0.018	0.022
L	0.22	0.32	0.008	0.013
L1	0.22	0.32	0.008	0.013
e	Typ. 0.34		Typ. 0.013	
e1	Typ. 0.65		Typ. 0.026	